MC74LVX14

Hex Schmitt Inverter

With 5 V-Tolerant Inputs

The MC74LVX14 is an advanced high speed CMOS Schmitt inverter. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

The MC74LVX14 is pin and functionally compatible to the MC74LVX04, but the inputs have hysteresis and, with its Schmitt trigger function, can be used as a line receiver which will receive slow input signals.

Features

- High Speed: $t_{PD} = 6.8 \text{ ns}$ (Typ) at $V_{CC} = 3.3 \text{ V}$
- Low Power Dissipation: $I_{CC} = 2 \mu A$ (Max) at $T_A = 25^{\circ}C$
- Powerdown Protection Provided on Inputs
- Balanced Propagation Delays
- Low Noise: $V_{OLP} = 0.5 \text{ V (Max)}$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: Human Body Model > 2000 V;
 - Machine Model > 200 V
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

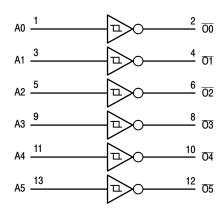


Figure 1. Logic Diagram

PIN NAMES

Pins	Function
An	Data Inputs
On	Data Outputs

FUNCTION TABLE

An	On
Т	H L



ON Semiconductor®

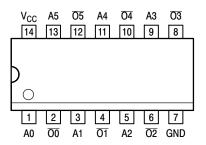
http://onsemi.com





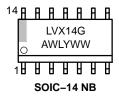
SOIC-14 NB D SUFFIX CASE 751A TSSOP-14 DT SUFFIX CASE 948G

PIN ASSIGNMENT



14-Lead (Top View)

MARKING DIAGRAMS





TSSOP-14

LVX14 = Specific Device Code A = Assembly Location

WL, L = Wafer Lot
Y = Year
WW, W = Work Week
G or = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

MC74LVX14

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V
V _{in}	DC Input Voltage	-0.5 to +7.0	V
V _{out}	DC Output Voltage	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Diode Current	-20	mA
I _{OK}	Output Diode Current	±20	mA
l _{out}	DC Output Current, per Pin	±25	mA
Icc	DC Supply Current, V _{CC} and GND Pins	±50	mA
P_{D}	Power Dissipation	180	mW
T _{stg}	Storage Temperature	-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	3.6	V
V_{in}	DC Input Voltage	0	5.5	V
V_{out}	DC Output Voltage	0	V_{CC}	V
T_A	Operating Temperature, All Package Types	-40	+85	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			v _{cc}	1	T _A = 25°(;	$T_A = -40$	to 85°C	
Symbol	Parameter	Test Conditions	V	Min	Тур	Max	Min	Max	Unit
V _{T+}	Positive Threshold Voltage (Figure 4)		3.0			2.20		2.20	V
V _{T-}	Negative Threshold Voltage (Figure 4)		3.0	0.90			0.90		V
V _H	Hysteresis Voltage (Figure 4)		3.0	0.30		1.20	0.30	1.20	V
V _{OH}	High-Level Output Voltage (V _{in} = V _{IH} or V _{IL})	$\begin{split} I_{OH} &= -50 \; \mu\text{A} \\ I_{OH} &= -50 \; \mu\text{A} \\ I_{OH} &= -4 \; \text{mA} \end{split}$	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		V
V _{OL}	Low-Level Output Voltage (V _{in} = V _{IH} or V _{IL})	$I_{OL} = 50 \mu A$ $I_{OL} = 50 \mu A$ $I_{OL} = 4 \text{ mA}$	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44	V
l _{in}	Input Leakage Current	V _{in} = 5.5 V or GND	3.6			±0.1		±1.0	μΑ
I _{CC}	Quiescent Supply Current	$V_{in} = V_{CC}$ or GND	3.6			2.0		20.0	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$)

				T _A = 25°C		$T_A = -40 \text{ to } 85^{\circ}\text{C}$			
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Propagation Delay, Input-to-Output	V _{CC} = 2.7 V	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		8.7 11.2	16.3 19.8	1.0 1.0	19.5 23.0	ns
		$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		6.8 9.3	10.6 14.1	1.0 1.0	12.5 16.0	
toshl toslh	Output-to-Output Skew (Note 1)	$V_{CC} = 2.7 \text{ V}$ $V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 50 \text{ pF}$ $C_L = 50 \text{ pF}$			1.5 1.5		1.5 1.5	ns

Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

CAPACITIVE CHARACTERISTICS

		T _A = 25°C		T _A = -40 to 85°C			
Symbol	Parameter	Min	Тур	Max	Min	Max	Unit
Cin	Input Capacitance		4	10		10	pF
C _{PD}	Power Dissipation Capacitance (Note 2)		21				pF

^{2.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}/6$ (per buffer). C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 3.3$ V, Measured in SOIC Package)

	T _A =		25°C	
Symbol	Characteristic	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.3	0.5	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.3	-0.5	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		0.9	V

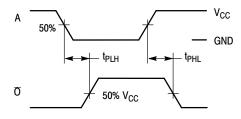
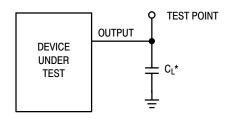


Figure 2. Switching Waveforms



*Includes all probe and jig capacitance

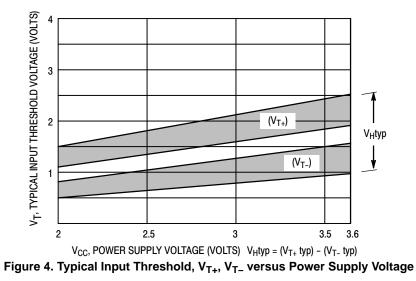
Figure 3. Test Circuit

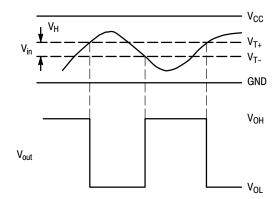
ORDERING INFORMATION

Device	Package	Shipping [†]
MC74LVX14DR2G	SOIC-14 NB (Pb-Free)	2500 Tape & Reel
MC74LVX14DTR2G	TSSOP-14 (Pb-Free)	2500 Tape & Reel
NLV74LVX14DTR2G*	TSSOP-14 (Pb-Free)	2500 Tape & Reel

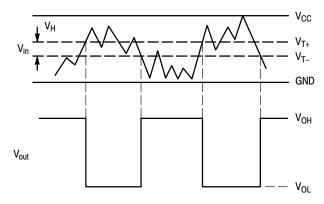
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.





(a) A Schmitt-Trigger Squares Up Inputs With Slow Rise and Fall Times



(b) A Schmitt-Trigger Offers Maximum Noise Immunity

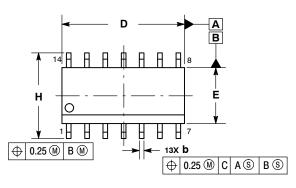
Figure 5. Typical Schmitt-Trigger Applications



△ 0.10

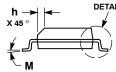
SOIC-14 NB CASE 751A-03 ISSUE L

DATE 03 FEB 2016





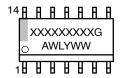




- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
 - ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 - DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT
- MAXIMUM MATERIAL CONDITION.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	1.35	1.75	0.054	0.068	
A1	0.10	0.25	0.004	0.010	
АЗ	0.19	0.25	0.008	0.010	
b	0.35	0.49	0.014	0.019	
D	8.55	8.75	0.337	0.344	
Е	3.80	4.00	0.150	0.157	
е	1.27	1.27 BSC		BSC	
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.019	
Ĺ	0.40	1.25	0.016	0.049	
М	0 °	7°	0 °	7°	

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year WW = Work Week G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator. "G" or microdot " ■". may or may not be present.

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

C SEATING PLANE

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42565B	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	SOIC-14 NB		PAGE 1 OF 2		

ON Semiconductor and un are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

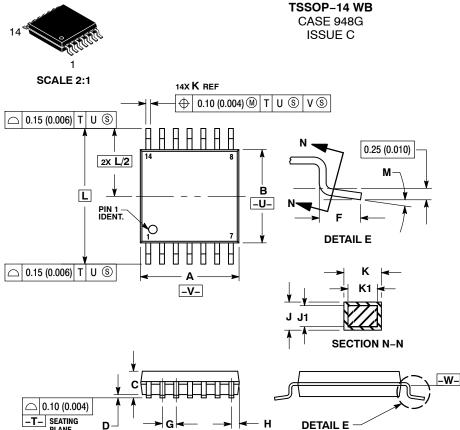
SOIC-14 CASE 751A-03 ISSUE L

DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

DOCUMENT NUMBER:	98ASB42565B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOIC-14 NB		PAGE 2 OF 2	

ON Semiconductor and IN are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.



DATE 17 FEB 2016

- NOTES.

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

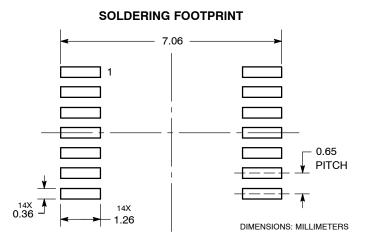
 3. DIMENSION A DOES NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

 6. TERMINAL NUMBERS ARE SHOWN FOR DECEDEDIC ONLY
- REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE
 DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С	-	1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	0°	8°	0°	8 °

GENERIC MARKING DIAGRAM*





= Assembly Location

= Wafer Lot = Year

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DOCUMENT NUMBER:	98ASH70246A	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	TSSOP-14 WB		PAGE 1 OF 1	

ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.